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LANGUAGES

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FORMATION

1999

Postgraduate Diploma in Solid State Physics.
University of Constantine

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Magister Diploma in Semiconductor Physics
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Doctorate degree in Semiconductor Physics
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University Habilitation Diploma in Physics.
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1- N. Merabtine, S. Khemissi, M. Zaabat, M. Belgat, C. Kenzai

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5- S. Kattar, S. Khemissi,

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